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November 2013

## IRLM220A

# N-Channel A-FET 200 V, 1.13 A, 800 mΩ

#### **FEATURES**

v Avalanche Rugged Technology

v Rugged Gate Oxide Technology

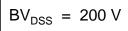
v Lower Input Capacitance

v Improved Gate Charge

v Extended Safe Operating Area

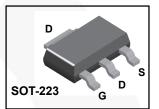
ν Lower Leakage Current : 10 μA (Max.) @  $V_{DS}$  = 200V

ν Lower R<sub>DS(ON)</sub> : 0.609 Ω (Typ.)



 $R_{DS(on)} = 0.8 \Omega$ 

 $I_D = 1.13 A$ 



### **Absolute Maximum Ratings**

Symbol	Characteristic	IRLM220ATF	Units		
V <sub>DSS</sub>	Drain-to-Source Voltage	200	V		
,	Continuous Drain Current (T <sub>A</sub> =25°C)		1.13	•	
I <sub>D</sub>	Continuous Drain Current (T <sub>A</sub> =70°C)	0.9	А		
I <sub>DM</sub>	Drain Current-Pulsed (	(1)	9	Α	
$V_{GS}$	Gate-to-Source Voltage		±20	V	
E <sub>AS</sub>			29	mJ	
I <sub>AR</sub>	Avalanche Current (	(1)	1.13	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy (	(1)	0.2	mJ	
dv/dt	Peak Diode Recovery dv/dt (	(3)	5	V/ns	
$P_{D}$	Total Power Dissipation (T <sub>A</sub> =25°C) *		2	W	
. Б	Linear Derating Factor *		0.016	W/°C	
	Operating Junction and		55 / 450		
$T_J$ , $T_STG$	Storage Temperature Range		- 55 to +150	°C	
	Maximum Lead Temp. for Soldering		000		
T <sub>L</sub>	Purposes, 1/8" from case for 5-seconds	s	300		

#### Thermal Resistance

Symbol	Characteristic	Тур.	Units	
$R_{ heta JA}$	Junction-to-Ambient *		62.5	°C/W

<sup>\*</sup> When mounted on the minimum pad size recommended (PCB Mount).

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
IRLM220ATF	IRLM220A	SOT-223	Tape and Reel	13 "	12 mm	4000 units

### Electrical Characteristics $T_c = 25^{\circ}C$ unless otherwise noted.

Symbol	Characteristic		Тур.	Max.	Units	Test Condition	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	200			V	$V_{GS} = 0V, I_{D} = 250 \mu A$	
$\Delta \text{BV}/\Delta \text{T}_{\text{J}}$	Breakdown Voltage Temp. Coeff.		0.18	2.0	V/°C	I <sub>D</sub> =250μA <b>See Fig 7</b>	
$V_{GS(th)}$	Gate Threshold Voltage	1.0	-	100	V	$V_{DS} = 5V, I_{D} = 250 \mu A$	
	Gate-Source Leakage, Forward			-100	100 nA V <sub>GS</sub> =20V		
I <sub>GSS</sub>	Gate-Source Leakage, Reverse			10	IIA	V <sub>GS</sub> =20V	
	Basis to Course I solve a Course			100		V <sub>DS</sub> =200V	
I <sub>DSS</sub>	Drain-to-Source Leakage Current				μΑ	V <sub>DS</sub> =160V,T <sub>C</sub> =125°C	
	Static Drain-Source					\	
R <sub>DS(on)</sub>	On-State Resistance			0.8	Ω	$V_{GS}=5V,I_D=0.57A$	
g <sub>fs</sub>	Forward Transconductance		2.8		S	V <sub>DS</sub> =40V,I <sub>D</sub> =0.57A	
C <sub>iss</sub>	Input Capacitance		330	430		V 0V/V 05V/4 4MIL-	
C <sub>oss</sub>	Output Capacitance		55	70	pF $V_{GS}=0V,V_{DS}=25V,f=1MHz$ See Fig 5		
C <sub>rss</sub>	Reverse Transfer Capacitance		8	30			
t <sub>d(on)</sub>	Turn-On Delay Time		6	25		V 100VI FA	
t <sub>r</sub>	Rise Time		24	20		$V_{DD}=100V,I_{D}=5A,$	
$t_{d(off)}$	Turn-Off Delay Time		6	60	ns	$R_{G}=9\Omega$	
t <sub>f</sub>	Fall Time		6	20		<b>See Fig 13</b> (4)	
$Q_g$	Total Gate Charge		10.3	15		V <sub>DS</sub> =160V,V <sub>GS</sub> =5V,	
$Q_{gs}$	Gate-Source Charge		2.0		nC	I <sub>D</sub> =5A	
$Q_gd$	Gate-Drain ("Miller") Charge	-	4.4			See Fig 6 & Fig 12 (4)	

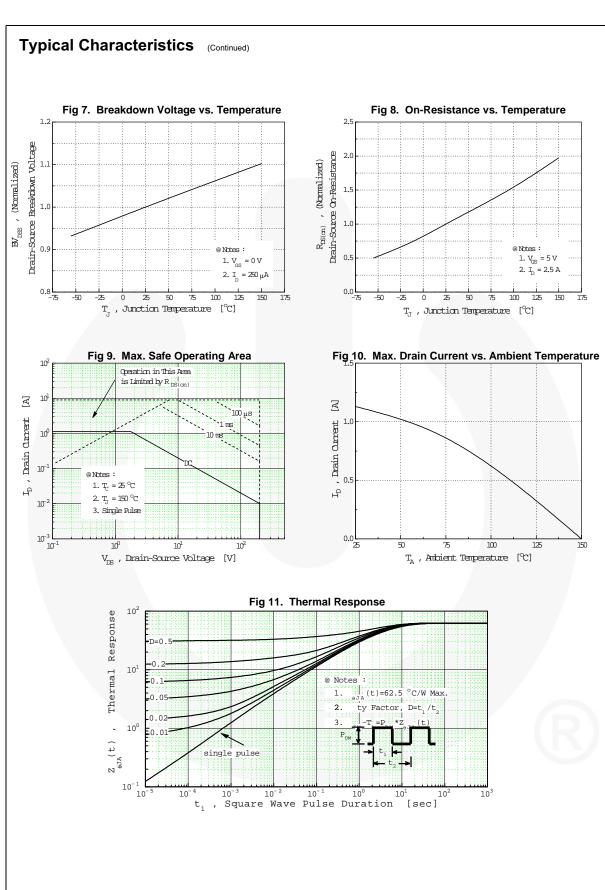
## Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic		Тур.	Max.	Units	Test Condition
Is	Continuous Source Current			1.13	^	Integral reverse pn-diode
I <sub>SM</sub>	Pulsed-Source Current (1)		-	9	Α	in the MOSFET
$V_{SD}$	Diode Forward Voltage	-	1	1.5	٧	T <sub>J</sub> =25°C,I <sub>S</sub> =1.13A,V <sub>GS</sub> =0V
t <sub>rr</sub>	Reverse Recovery Time		140	-	ns	$T_J=25$ °C, $I_F=5A$
Q <sub>rr</sub>	Reverse Recovery Charge		0.59	-	μС	di <sub>F</sub> /dt=100A/μs

#### Notes;

- ① Repetitive rating : pulse-width limited by maximum junction temperature.
- (2) L = 35 mH,  $I_{AS}$  = 1.13 A,  $V_{DD}$  = 50 V,  $R_G$  = 27  $\Omega$ , starting  $T_J$  = 25°C. (3)  $I_{SD} \le 5$  A, di/dt  $\le 180$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J$  = 25°C. (4) Essentially independent of operating temperature.

#### **Typical Characteristics** Fig 1. Output Characteristics Fig 2. Transfer Characteristics 10<sup>1</sup> Тар: 7.0V 60V 55V 5.0V $\mathbb{Z}$ 4.5V 4.0V 3.5V Drain Current $I_{\rm D}$ , Drain Current 100 150 °C 10<sup>0</sup> 25 °C @ Notes: 1. $V_{GS} = 0 V$ H<sup>2</sup> 10<sup>-1</sup> @ Notes : 2. $V_{DS} = 40 \text{ V}$ 1. 250 $\mu s$ Pulse Test 3. 250 $\mu s$ Pulse Test 2. T<sub>C</sub> = 25 °C 10-1 10 10 10 V<sub>DS</sub> , Drain-Source Voltage [V] $V_{CS}$ , Gate-Source Voltage [V] Fig 3. On-Resistance vs. Drain Current Fig 4. Source-Drain Diode Forward Voltage $\mathbb{Z}$ Drain-Source On-Resistance , Reverse Drain Current [Ω], $V_{GS} = 5 \text{ V}$ 100 @Notes: 1. V<sub>SS</sub> = 0 V Į, @Note: $T_J = 25$ °C 2. 250 μs Pulse Test 0.0 10 1.4 12 15 18 0.6 1.6 0.4 0.8 1.0 1.2 ${\bf I}_{\!\! {\rm D}}$ , Drain Current [A] $V_{SD}$ , Source-Drain Voltage [V] Fig 6. Gate Charge vs. Gate-Source Voltage Fig 5. Capacitance vs. Drain-Source Voltage $C_{iss} = C_{gs} + C_{gd} (C_{ds} = shorted)$ Coss = ds + Cod 400 $V_{DS} = 40 \text{ V}$ = 100 V뎐 $V_{_{\mathbb G}}$ , Gate-Source Voltage Capacitance 200 @Notes: 1. $V_{GS} = 0 \text{ V}$ 2. f = 1 MHz 100 @ Notes : $I_D = 5 A$ Q<sub>g</sub> , Total Gate Charge [nC] 10 V<sub>DS</sub> , Drain-Source Voltage [V]



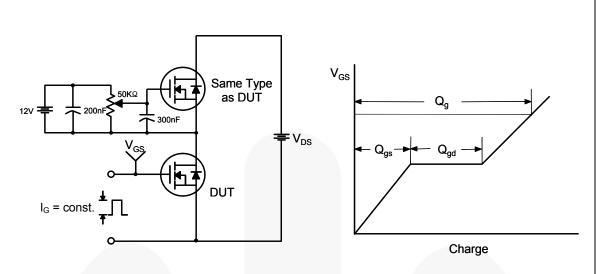


Figure 12. Gate Charge Test Circuit & Waveform

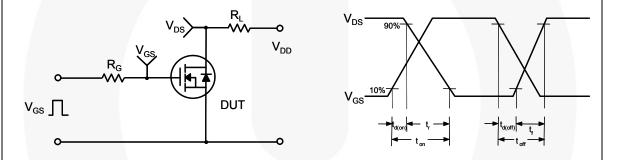


Figure 13. Resistive Switching Test Circuit & Waveforms

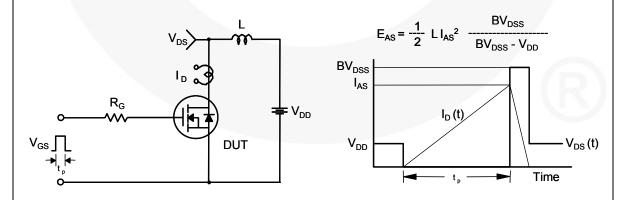
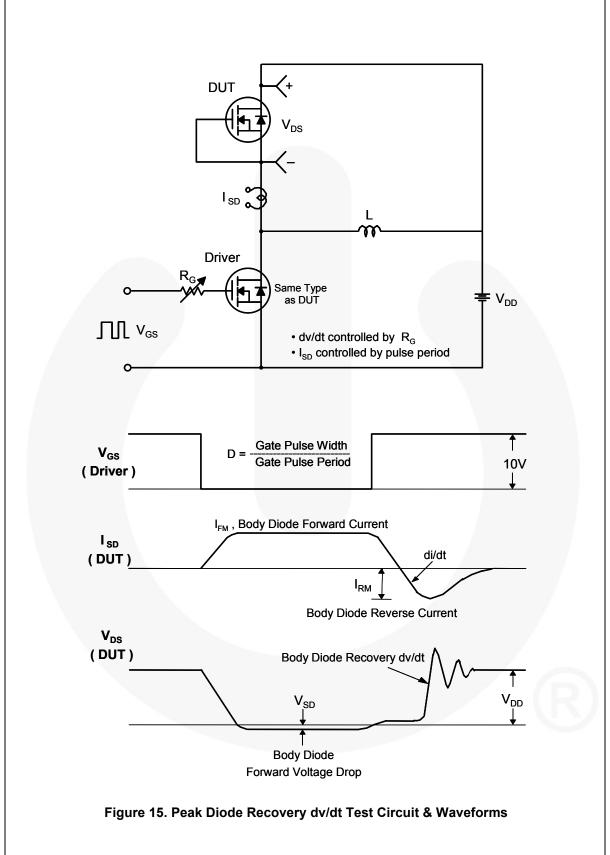


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



#### **Mechanical Dimensions**

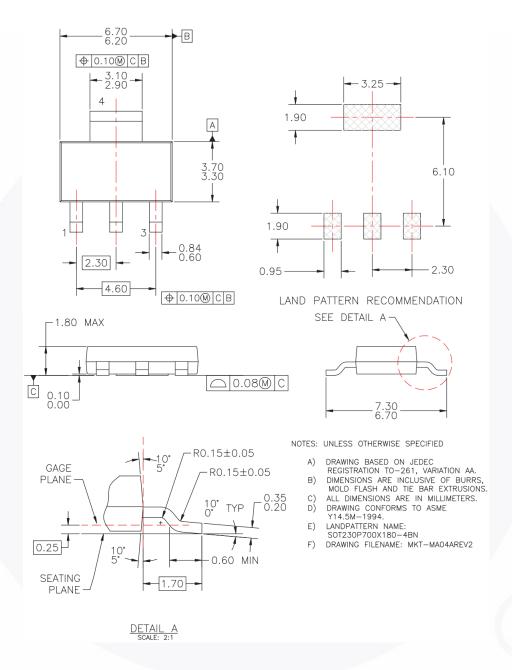


Figure 16. SOT-223, Molded, 4-Lead

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